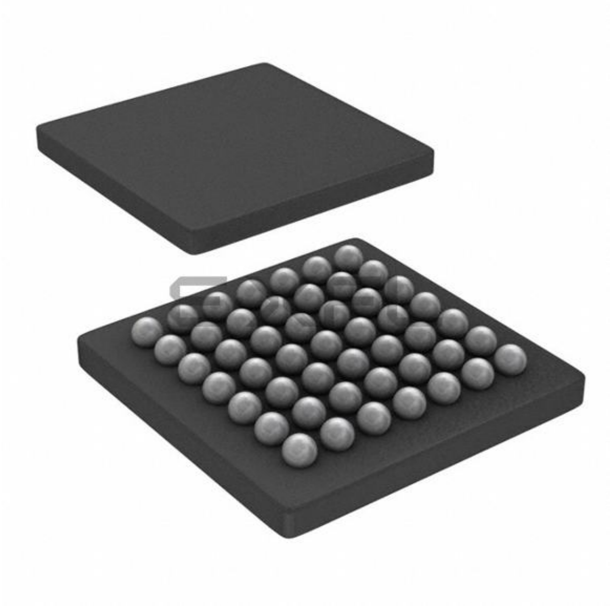
Lattice Semiconductor Corporation - LCMXO3LF-2100E-5UWG49ITR1K Datasheet



Welcome to **E-XFL.COM**

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	264
Number of Logic Elements/Cells	2112
Total RAM Bits	75776
Number of I/O	38
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	49-UFBGA, WLCSP
Supplier Device Package	49-WLCSP (3.11x3.19)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3lf-2100e-5uwg49itr1k

MachXO3 Family Data Sheet
Introduction

January 2016 **Advance Data Sheet DS1047**

Features

Solutions
- Smallest footprint, lowest power, high data throughput bridging solutions for mobile applications
- Optimized footprint, logic density, IO count, IO performance devices for IO management and logic applications
- High IO/logic, lowest cost/IO, high IO devices for IO expansion applications

Flexible Architecture
- Logic Density ranging from 640 to 9.4K LUT4
- High IO to LUT ratio with up to 384 IO pins

Advanced Packaging
- 0.4 mm pitch: 1K to 4K densities in very small footprint WLCSP (2.5 mm x 2.5 mm to 3.8 mm x 3.8 mm) with 28 to 63 IOs
- 0.5 mm pitch: 640 to 6.9K LUT densities in 6 mm x 6 mm to 10 mm x 10 mm BGA packages with up to 281 IOs
- 0.8 mm pitch: 1K to 9.4K densities with up to 384 IOs in BGA packages

Pre-Engineered Source Synchronous I/O
- DDR registers in I/O cells
- Dedicated gearing logic
- 7:1 Gearing for Display I/Os
- Generic DDR, DDRx2, DDRx4

High Performance, Flexible I/O Buffer
- Programmable sysIO™ buffer supports wide range of interfaces:
  - — LVCMOS 3.3/2.5/1.8/1.5/1.2
  - — LVTTL
  - — LVDS, Bus-LVDS, MLVDS, LVPECL
  - — MIPI D-PHY Emulated
  - — Schmitt trigger inputs, up to 0.5 V hysteresis
- Ideal for IO bridging applications
- I/Os support hot socketing
- On-chip differential termination
- Programmable pull-up or pull-down mode

Flexible On-Chip Clocking
- Eight primary clocks
- Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
- Up to two analog PLLs per device with fractional-n frequency synthesis
  - — Wide input frequency range (7 MHz to 400 MHz)

Non-volatile, Multi-time Programmable
- Instant-on
  - — Powers up in microseconds
- Optional dual boot with external SPI memory
- Single-chip, secure solution
- Programmable through JTAG, SPI or I^{2}C
- MachXO3L includes multi-time programmable NVCM
- MachXO3LF infinitely reconfigurable Flash
  - — Supports background programming of non-volatile memory

TransFR Reconfiguration
- In-field logic update while IO holds the system state

Enhanced System Level Support
- On-chip hardened functions: SPI, I^{2}C, timer/counter
- On-chip oscillator with 5.5% accuracy
- Unique TraceID for system tracking
- Single power supply with extended operating range
- IEEE Standard 1149.1 boundary scan
- IEEE 1532 compliant in-system programming

Applications
- Consumer Electronics
- Compute and Storage
- Wireless Communications
- Industrial Control Systems
- Automotive System

Low Cost Migration Path
- Migration from the Flash based MachXO3LF to the NVCM based MachXO3L
- Pin compatible and equivalent timing

Table 1-1. MachXO3L/LF Family Selection Guide

Features		**MachXO3L-640/ MachXO3LF-640**	**MachXO3L-1300/ MachXO3LF-1300**	**MachXO3L-2100/ MachXO3LF-2100**	**MachXO3L-4300/ MachXO3LF-4300**	**MachXO3L-6900/ MachXO3LF-6900**	**MachXO3L-9400/ MachXO3LF-9400**
LUTs		640	1300	2100	4300	6900	9400
Distributed RAM (kbits)		5	10	16	34	54	73
EBR SRAM (kbits)		64	64	74	92	240	432
Number of PLLs		1	1	1	2	2	2
Hardened Functions:	I^2C	2	2	2	2	2	2
	SPI	1	1	1	1	1	1
	Timer/Counter	1	1	1	1	1	1
	Oscillator	1	1	1	1	1	1
MIPI D-PHY Support		Yes	Yes	Yes	Yes	Yes	Yes
Multi Time Programmable NVCM		MachXO3L-640	MachXO3L-1300	MachXO3L-2100	MachXO3L-4300	MachXO3L-6900	MachXO3L-9400
Programmable Flash		MachXO3LF-640	MachXO3LF-1300	MachXO3LF-2100	MachXO3LF-4300	MachXO3LF-6900	MachXO3LF-9400
Packages		**IO**					
36-ball WLCSP[1] (2.5 mm x 2.5 mm, 0.4 mm)			28				
49-ball WLCSP[1] (3.2 mm x 3.2 mm, 0.4 mm)				38			
81-ball WLCSP[1] (3.8 mm x 3.8 mm, 0.4 mm)					63		
121-ball csfBGA[1] (6 mm x 6 mm, 0.5 mm)		100	100	100	100		
256-ball csfBGA[1] (9 mm x 9 mm, 0.5 mm)			206	206	206	206	206
324-ball csfBGA[1] (10 mm x 10 mm, 0.5 mm)				268	268	281	
256-ball caBGA[2] (14 mm x 14 mm, 0.8 mm)			206	206	206	206	206
324-ball caBGA[2] (15 mm x 15 mm, 0.8 mm)				279	279	279	
400-ball caBGA[2] (17 mm x 17 mm, 0.8 mm)					335	335	335
484-ball caBGA[2] (19 mm x 19 mm, 0.8 mm)							384

1. Package is only available for E=1.2 V devices.
2. Package is only available for C=2.5 V/3.3 V devices.

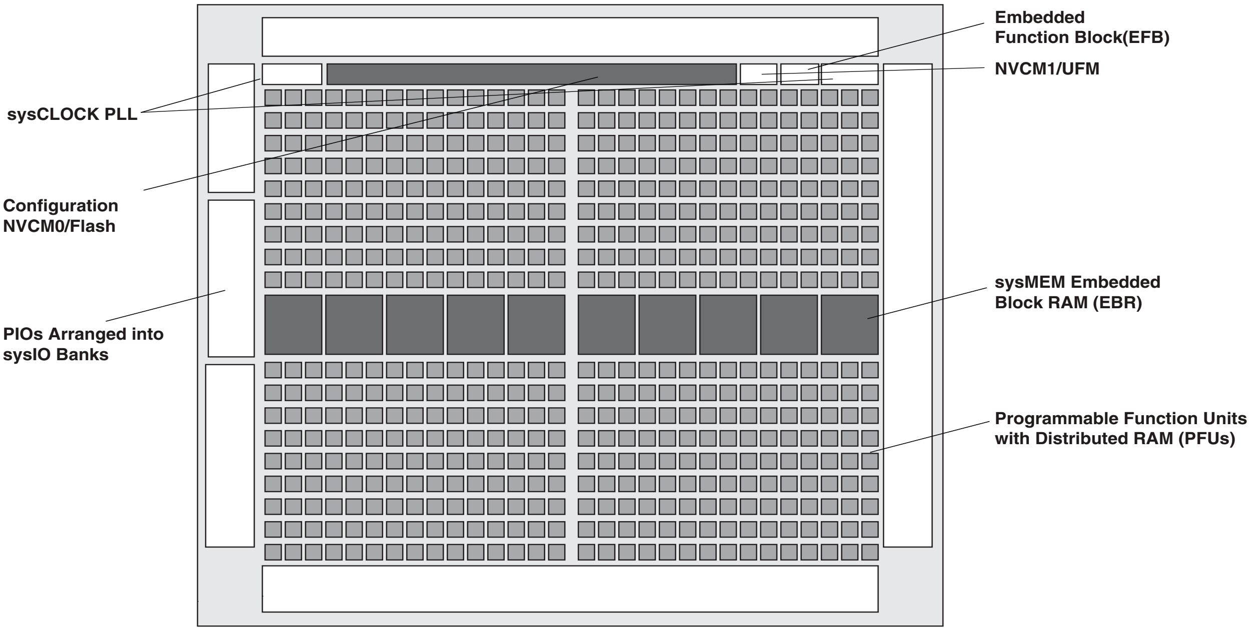
Introduction

MachXO3™ device family is an Ultra-Low Density family that supports the most advanced programmable bridging and IO expansion. It has the breakthrough IO density and the lowest cost per IO. The device IO features have the integrated support for latest industry standard IO.

The MachXO3L/LF family of low power, instant-on, non-volatile PLDs has five devices with densities ranging from 640 to 9400 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic these devices feature Embedded Block RAM (EBR), Distributed RAM, Phase Locked Loops (PLLs), pre-engineered source synchronous I/O support, advanced configuration support including dual-boot capability and hardened versions of commonly used functions such as SPI controller, I^2C controller and timer/counter. MachXO3LF devices also support User Flash Memory (UFM). These features allow these devices to be used in low cost, high volume consumer and system applications.

The MachXO3L/LF devices are designed on a 65nm non-volatile low power process. The device architecture has several features such as programmable low swing differential I/Os and the ability to turn off I/O banks, on-chip PLLs

Figure 2-2. Top View of the MachXO3L/LF-4300 Device



Notes:

- MachXO3L/LF-1300, MachXO3L/LF-2100, MachXO3L/LF-6900 and MachXO3L/LF-9400 are similar to MachXO3L/LF-4300. MachXO3L/LF-1300 has a lower LUT count, one PLL, and seven EBR blocks. MachXO3L/LF-2100 has a lower LUT count, one PLL, and eight EBR blocks. MachXO3L/LF-6900 has a higher LUT count, two PLLs, and 26 EBR blocks. MachXO3L/LF-9400 has a higher LUT count, two PLLs, and 48 EBR blocks.
- MachXO3L devices have NVCM, MachXO3LF devices have Flash.

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO3L/LF family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag “hard” control logic to minimize LUT usage.

The MachXO3L/LF registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO3L/LF architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. These blocks are located at the ends of the on-chip NVCM/Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO3L/LF devices provide commonly used hardened functions such as SPI controller, I^{2}C controller and timer/counter.

MachXO3LF devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I^{2}C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO3L/LF devices are available for operation from 3.3 V, 2.5 V and 1.2 V power sup-plies, providing easy integration into the overall system.

Table 2-4. PLL Signal Descriptions (Continued)

Port Name	I/O	Description
CLKOP	O	Primary PLL output clock (with phase shift adjustment)
CLKOS	O	Secondary PLL output clock (with phase shift adjust)
CLKOS2	O	Secondary PLL output clock2 (with phase shift adjust)
CLKOS3	O	Secondary PLL output clock3 (with phase shift adjust)
LOCK	O	PLL LOCK, asynchronous signal. Active high indicates PLL is locked to input and feedback signals.
DPHSRC	O	Dynamic Phase source – ports or WISHBONE is active
STDBY	I	Standby signal to power down the PLL
RST	I	PLL reset without resetting the M-divider. Active high reset.
RESETM	I	PLL reset - includes resetting the M-divider. Active high reset.
RESETC	I	Reset for CLKOS2 output divider only. Active high reset.
RESETD	I	Reset for CLKOS3 output divider only. Active high reset.
ENCLKOP	I	Enable PLL output CLKOP
ENCLKOS	I	Enable PLL output CLKOS when port is active
ENCLKOS2	I	Enable PLL output CLKOS2 when port is active
ENCLKOS3	I	Enable PLL output CLKOS3 when port is active
PLLCLK	I	PLL data bus clock input signal
PLLRST	I	PLL data bus reset. This resets only the data bus not any register values.
PLLSTB	I	PLL data bus strobe signal
PLLWE	I	PLL data bus write enable signal
PLLADDR [4:0]	I	PLL data bus address
PLLDATI [7:0]	I	PLL data bus data input
PLLDATO [7:0]	O	PLL data bus data output
PLLACK	O	PLL data bus acknowledge signal

sysMEM Embedded Block RAM Memory

The MachXO3L/LF devices contain sysMEM Embedded Block RAMs (EBRs). The EBR consists of a 9-Kbit RAM, with dedicated input and output registers. This memory can be used for a wide variety of purposes including data buffering, PROM for the soft processor and FIFO.

sysMEM Memory Block

The sysMEM block can implement single port, dual port, pseudo dual port, or FIFO memories. Each block can be used in a variety of depths and widths as shown in Table 2-5.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the NVCM or Configuration Flash.

MachXO3LF EBR initialization data can also be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO3LF devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

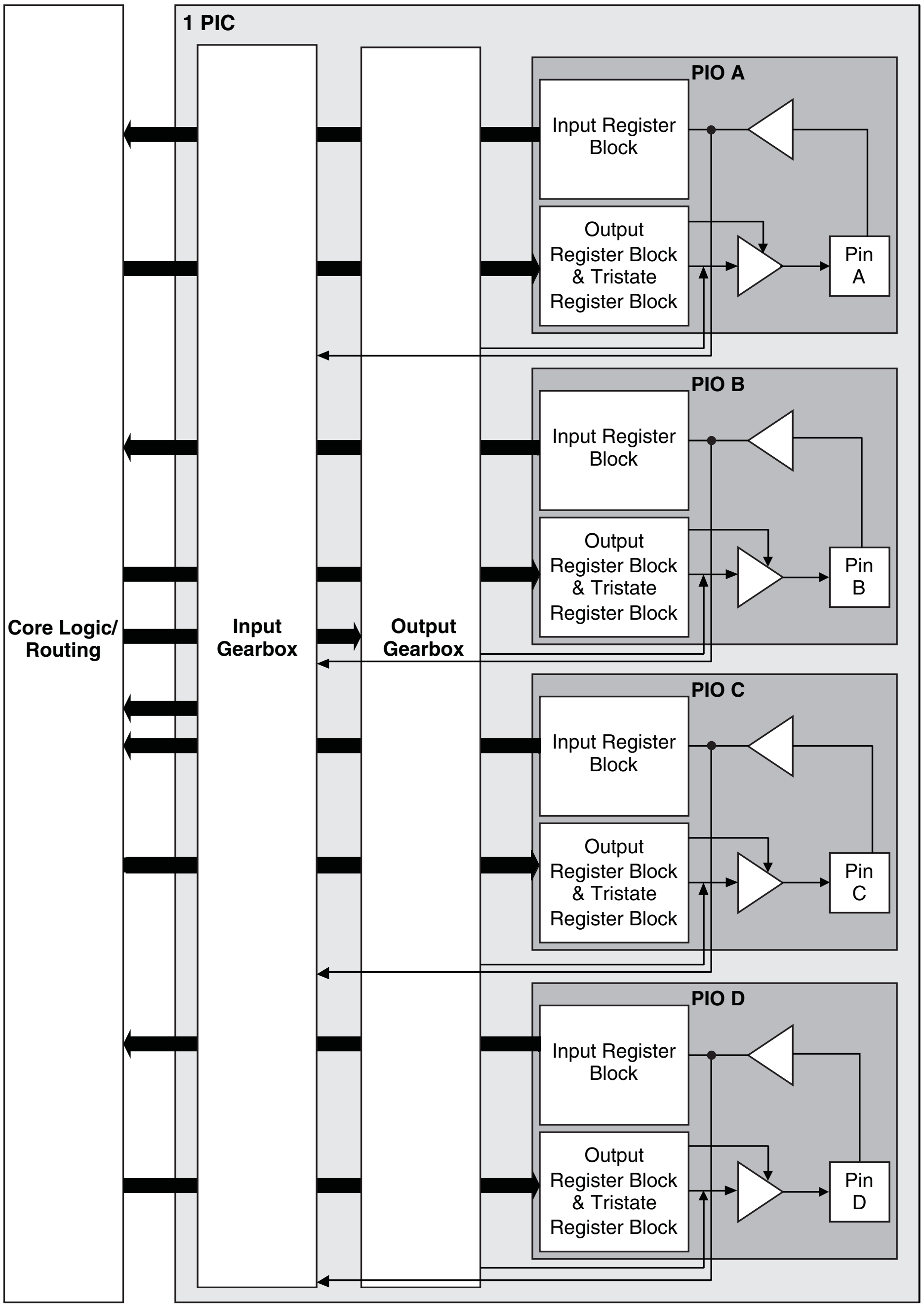
Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

Figure 2-11. Group of Four Programmable I/O Cells



Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysIO buffers.

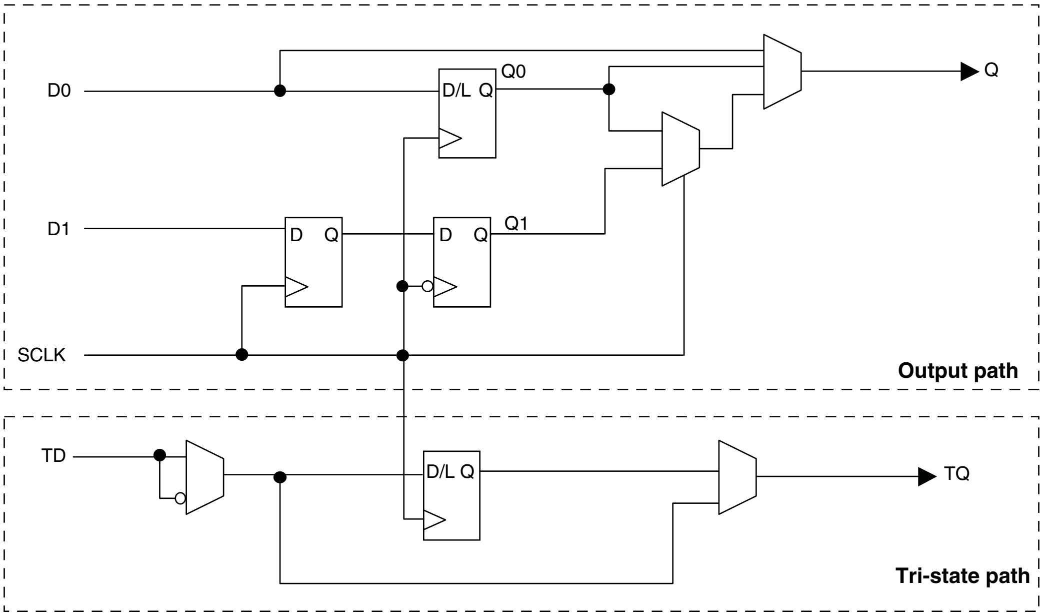
Left, Top, Bottom Edges

In SDR mode, D0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type register or latch.

In DDR generic mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the same clock is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-12 shows the output register block on the left, top and bottom edges.

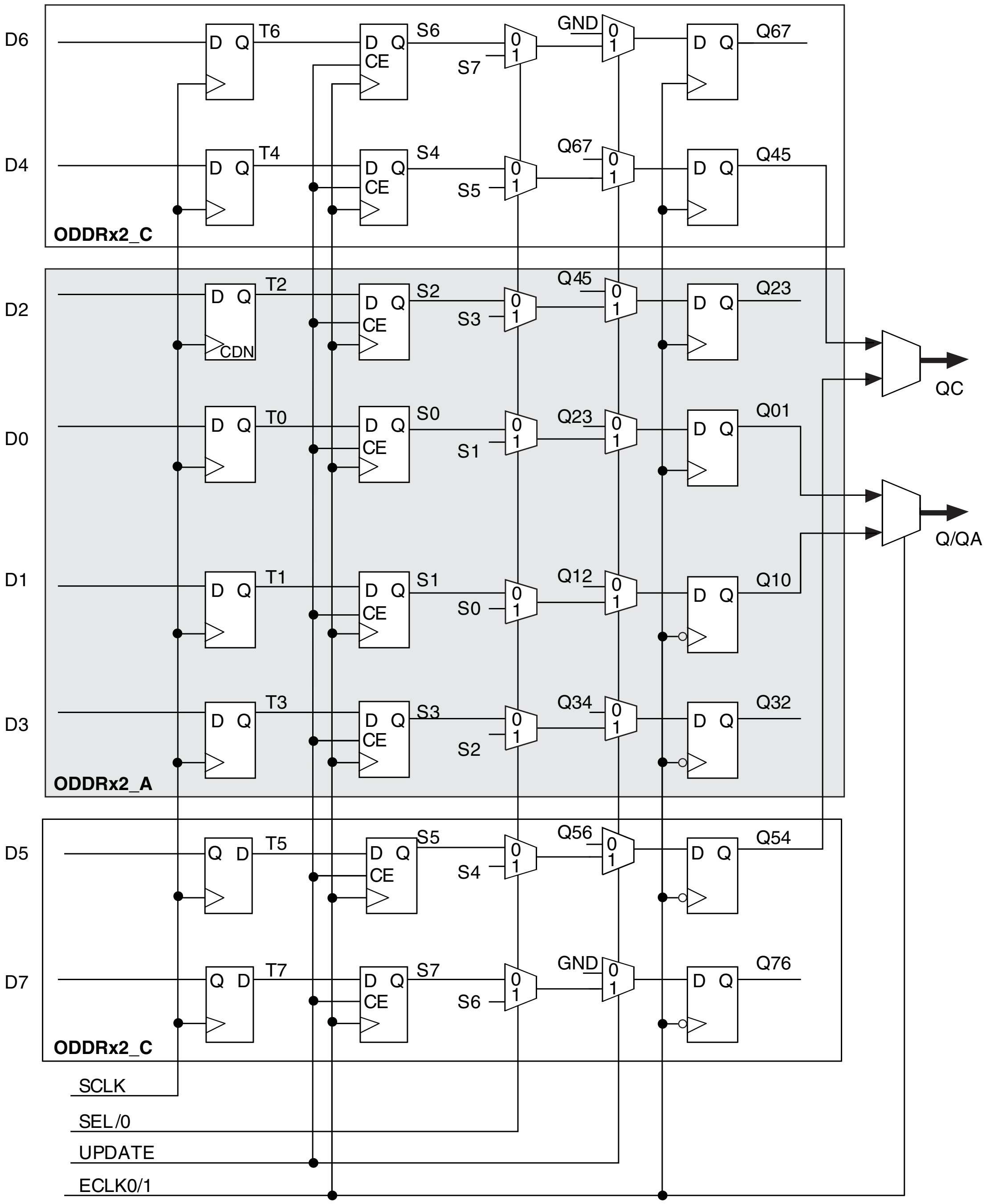
Figure 2-12. MachXO3L/LF Output Register Block Diagram (PIO on the Left, Top and Bottom Edges)



Tri-state Register Block

The tri-state register block registers tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output.

Figure 2-14. Output Gearbox



More information on the output gearbox is available in TN1281, Implementing High-Speed Interfaces with MachXO3 Devices.

Figure 2-15. MachXO3L/LF-1300 in 256 Ball Packages, MachXO3L/LF-2100, MachXO3L/LF-4300, MachXO3L/LF-6900 and MachXO3L/LF-9400 Banks

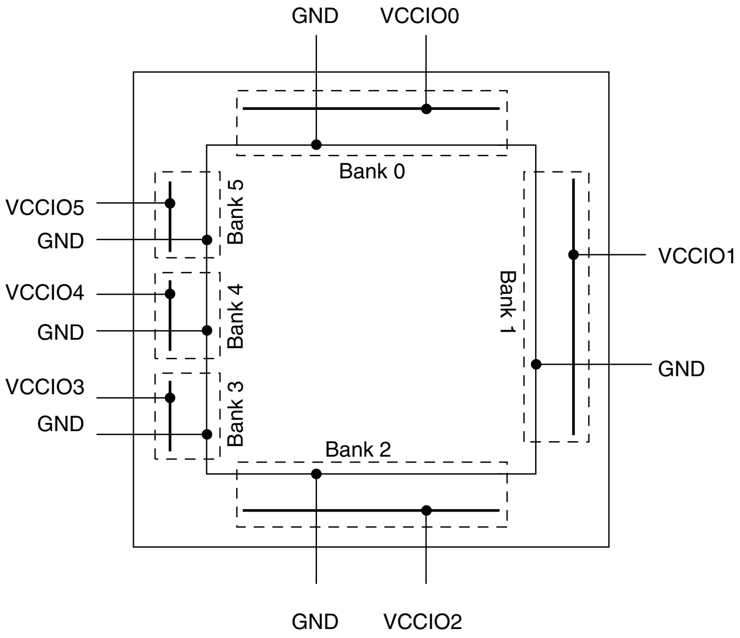
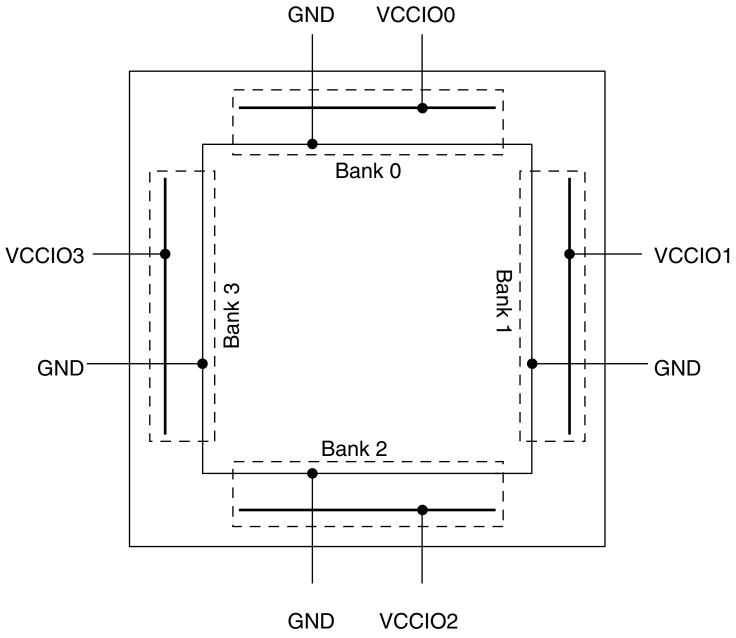


Figure 2-16. MachXO3L/LF-640 and MachXO3L/LF-1300 Banks



Configuration and Testing

This section describes the configuration and testing features of the MachXO3L/LF family.

IEEE 1149.1-Compliant Boundary Scan Testability

All MachXO3L/LF devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with V_{CCIO} Bank 0 and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, see AN8066, Boundary Scan Testability with Lattice sysIO Capability and TN1087, Minimizing System Interruption During Configuration Using TransFR Technology.

Device Configuration

All MachXO3L/LF devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration and the sysCONFIG port which supports serial configuration through I^2C or SPI. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are various ways to configure a MachXO3L/LF device:

1. Internal NVCM/Flash Download
2. JTAG
3. Standard Serial Peripheral Interface (Master SPI mode) – interface to boot PROM memory
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Standard I^2C Interface to system microprocessor

Upon power-up, the configuration SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port. Optionally the device can run a CRC check upon entering the user mode. This will ensure that the device was configured correctly.

The sysCONFIG port has 10 dual-function pins which can be used as general purpose I/Os if they are not required for configuration. See TN1279, MachXO3 Programming and Configuration Usage Guide for more information about using the dual-use pins as general purpose I/Os.

Lattice design software uses proprietary compression technology to compress bit-streams for use in MachXO3L/LF devices. Use of this technology allows Lattice to provide a lower cost solution. In the unlikely event that this technology is unable to compress bitstreams to fit into the amount of on-chip NVCM/Flash, there are a variety of techniques that can be utilized to allow the bitstream to fit in the on-chip NVCM/Flash. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

The Test Access Port (TAP) has five dual purpose pins (TDI, TDO, TMS, TCK and JTAGENB). These pins are dual function pins - TDI, TDO, TMS and TCK can be used as general purpose I/O if desired. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

TransFR (Transparent Field Reconfiguration)

TransFR is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a simple push-button solution. For more details refer to TN1087, Minimizing System Interruption During Configuration Using TransFR Technology for details.

Security and One-Time Programmable Mode (OTP)

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO3L/LF devices contain security bits that, when set, prevent the readback of the SRAM configuration and NVCM/Flash spaces. The device can be in one of two modes:

1. Unlocked – Readback of the SRAM configuration and NVCM/Flash spaces is allowed.
2. Permanently Locked – The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the NVCM/Flash and SRAM OTP portions of the device. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Password

The MachXO3LF supports a password-based security access feature also known as Flash Protect Key. Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. The Flash Protect Key feature provides a method of controlling access to the Configuration and Programming modes of the device. When enabled, the Configuration and Programming edit mode operations (including Write, Verify and Erase operations) are allowed only when coupled with a Flash Protect Key which matches that expected by the device. Without a valid Flash Protect Key, the user can perform only rudimentary non-configuration operations such as Read Device ID. For more details, refer to TN1313, Using Password Security with MachXO3 Devices.

Dual Boot

MachXO3L/LF devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the external SPI Flash. The golden image MUST reside in an on-chip NVCM/Flash. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Soft Error Detection

The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1292, MachXO3 Soft Error Detection Usage Guide.

Soft Error Correction

The MachXO3LF device supports Soft Error Correction (SEC). Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. When BACKGROUND_RECONFIG is enabled using the Lattice Diamond Software in a design, asserting the PROGRAMN pin or issuing the REFRESH sysConfig command refreshes the SRAM array from configuration memory. Only the detected error bit is corrected. No other SRAM cells are changed, allowing the user design to function uninterrupted.

During the project design phase, if the overall system cannot guarantee containment of the error or its subsequent effects on downstream data or control paths, Lattice recommends using SED only. The MachXO3 can be then be soft-reset by asserting PROGRAMN or issuing the Refresh command over a sysConfig port in response to SED. Soft-reset additionally erases the SRAM array prior to the SRAM refresh, and asserts internal Reset circuitry to guarantee a known state. For more details, refer to TN1292, MachXO3 Soft Error Detection (SED)/Correction (SEC) Usage Guide.

MachXO3 Family Data Sheet
DC and Switching Characteristics

February 2017 **Advance Data Sheet DS1047**

Absolute Maximum Ratings[1, 2, 3]

	MachXO3L/LF E (1.2 V)	**MachXO3L/LF C (2.5 V/3.3 V)**
Supply Voltage V_{CC}	–0.5 V to 1.32 V	–0.5 V to 3.75 V
Output Supply Voltage V_{CCIO}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
I/O Tri-state Voltage Applied[4, 5]	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Dedicated Input Voltage Applied[4]	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Storage Temperature (Ambient)	–55 °C to 125 °C	–55 °C to 125 °C
Junction Temperature (T_J)	–40 °C to 125 °C	–40 °C to 125 °C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of –2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.
5. The dual function I^2C pins SCL and SDA are limited to –0.25 V to 3.75 V or to –0.3 V with a duration of <20 ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}[1]	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
	Core Supply Voltage for 2.5 V/3.3 V Devices	2.375	3.465	V
V_{CCIO}[1, 2, 3]	I/O Driver Supply Voltage	1.14	3.465	V
t_{JCOM}	Junction Temperature Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature Industrial Operation	–40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both the same voltage, they must also be the same supply.
2. See recommended voltages by I/O standard in subsequent table.
3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

Power Supply Ramp Rates[1]

Symbol	Parameter	Min.	Typ.	Max.	Units
t_{RAMP}	Power supply ramp rates for all power supplies.	0.01	—	100	V/ms

1. Assumes monotonic ramp rates.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} - 0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} - 0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < $V_{IN} < V_{CCIO}$	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	–309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < $V_{IN} < V_{CCIO}$	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \le V_{IN} \le V_{CCIO}$	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	$0 \le V_{IN} \le V_{CCIO}$	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pf
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6mA can occur on the high-to-low transition. For true LVDS output pins in MachXO3L/LF devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1280, MachXO3 sysIO Usage Guide.

sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of the MachXO3L/LF PLD family.

LVDS

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
V_{INP}, V_{INM}	Input Voltage	V_{CCIO} = 3.3 V	0	—	2.605	V
		V_{CCIO} = 2.5 V	0	—	2.05	V
V_{THD}	Differential Input Threshold		±100	—		mV
V_{CM}	Input Common Mode Voltage	V_{CCIO} = 3.3 V	0.05	—	2.6	V
		V_{CCIO} = 2.5 V	0.05	—	2.0	V
I_{IN}	Input current	Power on	—	—	±10	µA
V_{OH}	Output high voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	—	1.375	—	V
V_{OL}	Output low voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	0.90	1.025	—	V
V_{OD}	Output voltage differential	(V_{OP} - V_{OM}), R_T = 100 Ohm	250	350	450	mV
ΔV_{OD}	Change in V_{OD} between high and low		—	—	50	mV
V_{OS}	Output voltage offset	(V_{OP} - V_{OM})/2, R_T = 100 Ohm	1.125	1.20	1.395	V
ΔV_{OS}	Change in V_{OS} between H and L		—	—	50	mV
I_{OSD}	Output short circuit current	V_{OD} = 0 V driver outputs shorted	—	—	24	mA

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		7	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS, CLKOS2)		1.5625	400	MHz
f_{OUT2}	Output Frequency (CLKOS3 cascaded from CLKOS2)		0.0122	400	MHz
f_{VCO}	PLL VCO Frequency		200	800	MHz
f_{PFD}	Phase Detector Input Frequency		7	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	Without duty trim selected[3]	45	55	%
t_{DT_TRIM}[7]	Edge Duty Trim Accuracy		–75	75	%
t_{PH}[4]	Output Phase Accuracy		–6	6	%
t_{OPJIT}[1, 8]	Output Clock Period Jitter	$f_{OUT} > 100$ MHz	—	150	ps p-p
		$f_{OUT} < 100$ MHz	—	0.007	UIPP
	Output Clock Cycle-to-cycle Jitter	$f_{OUT} > 100$ MHz	—	180	ps p-p
		$f_{OUT} < 100$ MHz	—	0.009	UIPP
	Output Clock Phase Jitter	$f_{PFD} > 100$ MHz	—	160	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
	Output Clock Period Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
	Output Clock Cycle-to-cycle Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	–120	120	ps
t_W	Output Clock Pulse Width	At 90% or 10%[3]	0.9	—	ns
t_{LOCK}[2, 5]	PLL Lock-in Time		—	15	ms
t_{UNLOCK}	PLL Unlock Time		—	50	ns
t_{IPJIT}[6]	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{STABLE}[5]	STANDBY High to PLL Stable		—	15	ms
t_{RST}	RST/RESETM Pulse Width		1	—	ns
t_{RSTREC}	RST Recovery Time		1	—	ns
t_{RST_DIV}	RESETC/D Pulse Width		10	—	ns
t_{RSTREC_DIV}	RESETC/D Recovery Time		1	—	ns
$t_{ROTATE\text{-}SETUP}$	PHASESTEP Setup Time		10	—	ns
t_{ROTATE_WD}	PHASESTEP Pulse Width		4	—	VCO Cycles

1. Period jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock. Cycle-to-cycle jitter is taken over 1000 cycles. Phase jitter is taken over 2000 cycles. All values per JESD65B.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. CLKOS as compared to CLKOP output for one phase step at the maximum VCO frequency. See TN1282, MachXO3 sysCLOCK PLL Design and Usage Guide for more details.
5. At minimum f_{PFD}. As the f_{PFD} increases the time will decrease to approximately 60% the value listed.
6. Maximum allowed jitter on an input clock. PLL unlock may occur if the input jitter exceeds this specification. Jitter on the input clock may be transferred to the output clocks, resulting in jitter measurements outside the output specifications listed in this table.
7. Edge Duty Trim Accuracy is a percentage of the setting value. Settings available are 70 ps, 140 ps, and 280 ps in addition to the default value of none.
8. Jitter values measured with the internal oscillator operating. The jitter values will increase with loading of the PLD fabric and in the presence of SSO noise.

sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t_{PRGM}	PROGRAMN low pulse accept		55	—	ns
t_{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t_{INITL}	INITN low time	LCMXO3L/LF-640/ LCMXO3L/LF-1300	—	55	us
		LCMXO3L/LF-1300 256-Ball Package/ LCMXO3L/LF-2100	—	70	us
		LCMXO3L/LF-2100 324-Ball Package/ LCMXO3-4300	—	105	us
		LCMXO3L/LF-4300 400-Ball Package/ LCMXO3-6900	—	130	us
		LCMXO3L/LF-9400C	—	175	us
$t_{DPPINIT}$	PROGRAMN low to INITN low		—	150	ns
$t_{DPPDONE}$	PROGRAMN low to DONE low		—	150	ns
t_{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f_{MAX}	CCLK clock frequency		—	66	MHz
t_{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t_{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t_{STSU}	CCLK setup time		2	—	ns
t_{STH}	CCLK hold time		0	—	ns
t_{STCO}	CCLK falling edge to valid output		—	10	ns
t_{STOZ}	CCLK falling edge to valid disable		—	10	ns
t_{STOV}	CCLK falling edge to valid enable		—	10	ns
t_{SCS}	Chip select high time		25	—	ns
t_{SCSS}	Chip select setup time		3	—	ns
t_{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f_{MAX}	MCLK clock frequency		—	133	MHz
t_{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t_{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t_{STSU}	MCLK setup time		5	—	ns
t_{STH}	MCLK hold time		1	—	ns
t_{CSSPI}	INITN high to chip select low		100	200	ns
t_{MCLK}	INITN high to first MCLK edge		0.75	1	us

Pin Information Summary

	MachXO3L/LF -640	MachXO3L/LF-1300			
	CSFBGA121	WLCSP36	CSFBGA121	CSFBGA256	CABGA256
General Purpose IO per Bank					
Bank 0	24	15	24	50	50
Bank 1	26	0	26	52	52
Bank 2	26	9	26	52	52
Bank 3	24	4	24	16	16
Bank 4	0	0	0	16	16
Bank 5	0	0	0	20	20
Total General Purpose Single Ended IO	100	28	100	206	206
Differential IO per Bank					
Bank 0	12	8	12	25	25
Bank 1	13	0	13	26	26
Bank 2	13	4	13	26	26
Bank 3	11	2	11	8	8
Bank 4	0	0	0	8	8
Bank 5	0	0	0	10	10
Total General Purpose Differential IO	49	14	49	103	103
Dual Function IO	33	25	33	33	33
Number 7:1 or 8:1 Gearboxes					
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	7	3	7	14	14
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	7	2	7	14	14
High-speed Differential Outputs					
Bank 0	7	3	7	14	14
VCCIO Pins					
Bank 0	1	1	1	4	4
Bank 1	1	0	1	3	4
Bank 2	1	1	1	4	4
Bank 3	3	1	3	2	1
Bank 4	0	0	0	2	2
Bank 5	0	0	0	2	1
VCC	4	2	4	8	8
GND	10	2	10	24	24
NC	0	0	0	0	1
Reserved for Configuration	1	1	1	1	1
Total Count of Bonded Pins	**121**	**36**	**121**	**256**	**256**

MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-640E-5MG121C	640	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-6MG121C	640	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-5MG121I	640	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-640E-6MG121I	640	1.2 V	6	Halogen-Free csfBGA	121	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-1300E-5UWG36CTR	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR50	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36ITR	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR50	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5MG121C	1300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-6MG121C	1300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-5MG121I	1300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-6MG121I	1300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-5MG256C	1300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-6MG256C	1300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-5MG256I	1300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300E-6MG256I	1300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300C-5BG256C	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-6BG256C	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-5BG256I	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-1300C-6BG256I	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-2100E-5UWG49CTR	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR50	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49ITR	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR50	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5MG121C	2100	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-6MG121C	2100	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-5MG121I	2100	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-6MG121I	2100	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-5MG256C	2100	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-6MG256C	2100	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-5MG256I	2100	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-6MG256I	2100	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-5MG324C	2100	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-6MG324C	2100	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-5MG324I	2100	1.2 V	5	Halogen-Free csfBGA	324	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-2100E-6MG324I	2100	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3LF-2100C-5BG256C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-2100C-6BG256C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-2100C-5BG256I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-2100C-6BG256I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3LF-2100C-5BG324C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3LF-2100C-6BG324C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3LF-2100C-5BG324I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3LF-2100C-6BG324I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-4300E-5UWG81CTR	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3LF-4300E-5UWG81CTR50	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3LF-4300E-5UWG81CTR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3LF-4300E-5UWG81ITR	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3LF-4300E-5UWG81ITR50	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3LF-4300E-5UWG81ITR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3LF-4300E-5MG121C	4300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-4300E-6MG121C	4300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-4300E-5MG121I	4300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-4300E-6MG121I	4300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-4300E-5MG256C	4300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-4300E-6MG256C	4300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-4300E-5MG256I	4300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-4300E-6MG256I	4300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-4300E-5MG324C	4300	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3LF-4300E-6MG324C	4300	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3LF-4300E-5MG324I	4300	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3LF-4300E-6MG324I	4300	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3LF-4300C-5BG256C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-4300C-6BG256C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-4300C-5BG256I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-4300C-6BG256I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3LF-4300C-5BG324C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3LF-4300C-6BG324C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3LF-4300C-5BG324I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3LF-4300C-6BG324I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3LF-4300C-5BG400C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3LF-4300C-6BG400C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3LF-4300C-5BG400I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3LF-4300C-6BG400I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND

Date	Version	Section	Change Summary
April 2016	1.6	Introduction	Updated Features section. — Revised logic density range and IO to LUT ratio under Flexible Architecture. — Revised 0.8 mm pitch information under Advanced Packaging. — Added MachXO3L-9400/MachXO3LF-9400 information to Table 1-1, MachXO3L/LF Family Selection Guide.
			Updated Introduction section. — Changed density from 6900 to 9400 LUTs. — Changed caBGA packaging to 19 x 19 mm.
		Architecture	Updated Architecture Overview section. — Changed statement to “All logic density devices in this family...” — Updated Figure 2-2 heading and notes.
			Updated sysCLOCK Phase Locked Loops (PLLs) section. — Changed statement to “All MachXO3L/LF devices have one or more sysCLOCK PLL.”
			Updated Programmable I/O Cells (PIC) section. — Changed statement to “All PIO pairs can implement differential receivers.”
			Updated sysIO Buffer Banks section. Updated Figure 2-5 heading.
			Updated Device Configuration section. Added Password and Soft Error Correction.
		DC and Switching Characteristics	Updated Static Supply Current – C/E Devices section. Added LCMXO3L/LF-9400C and LCMXO3L/LF-9400E devices.
			Updated Programming and Erase Supply Current – C/E Devices section. — Added LCMXO3L/LF-9400C and LCMXO3L/LF-9400E devices. — Changed LCMXO3L/LF-640E and LCMXO3L/LF-1300E Typ. values.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. Added MachXO3L/LF-9400 devices.
			Updated NVCM/Flash Download Time section. Added LCMXO3L/LF-9400C device.
			Updated sysCONFIG Port Timing Specifications section. — Added LCMXO3L/LF-9400C device. — Changed t_{INITL} units to from ns to us. — Changed $t_{DPPINIT}$ and $t_{DPPDONE}$ Max. values are per PCN#03A-16.
		Pinout Information	Updated Pin Information Summary section. Added LCMXO3L/LF-9400C device.
		Ordering Information	Updated MachXO3 Part Number Description section. — Added 9400 = 9400 LUTs. — Added BG484 package.
			Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.